
2SC4680

Silicon NPN Epitaxial

HITACHI

Application

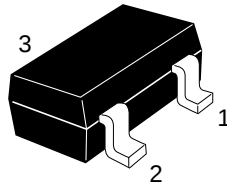
VHF / UHF high frequency switching

Features

- Low R_{on} and high performance for RF switch.
- Capable of high density mounting.

Outline

MPAK



1. Emitter
2. Base
3. Collector

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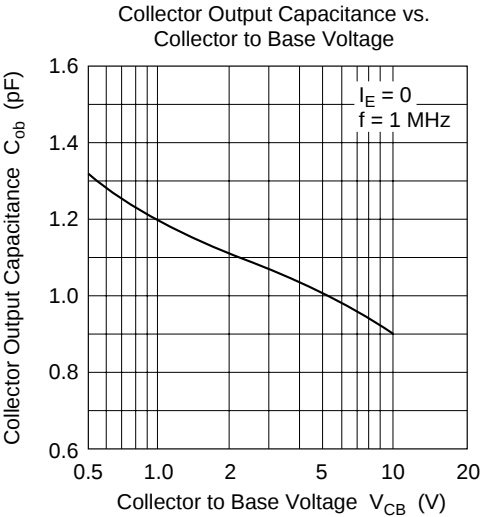
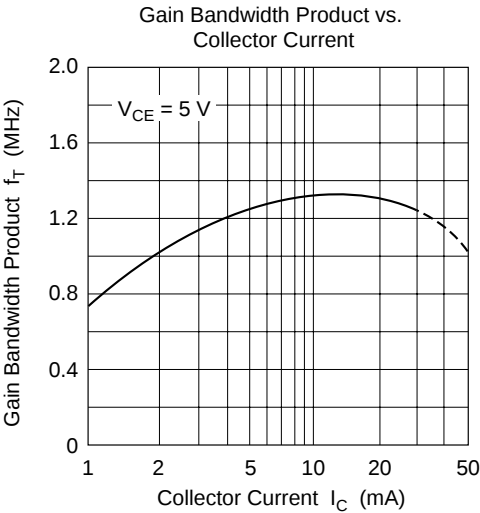
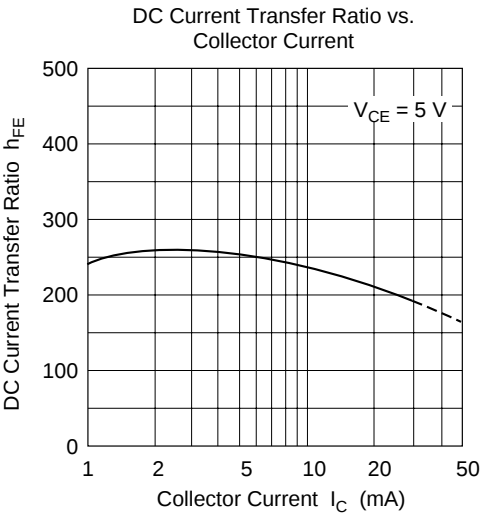
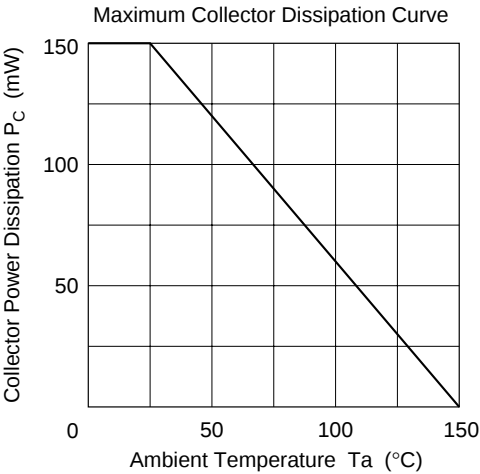
Absolute Maximum Ratings (Ta = 25°C)

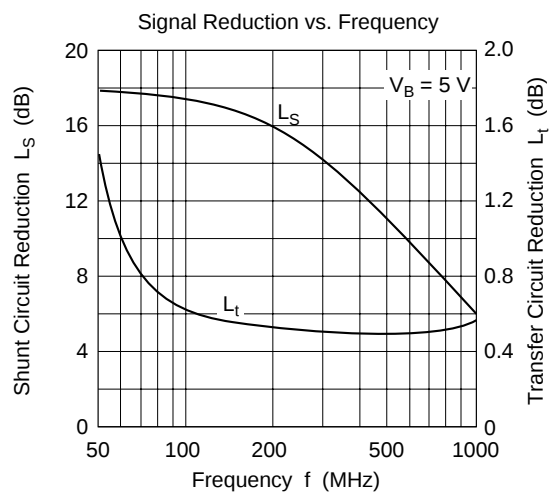
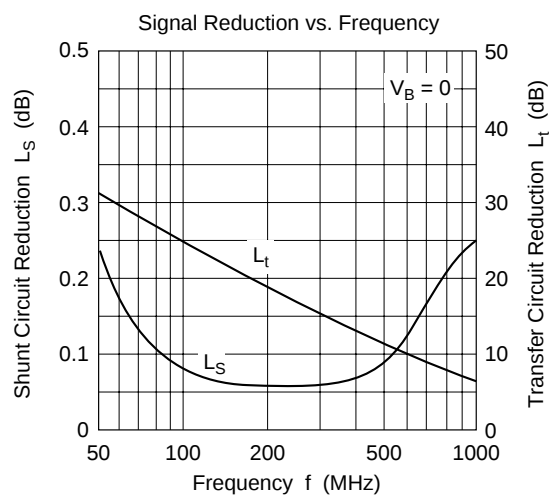
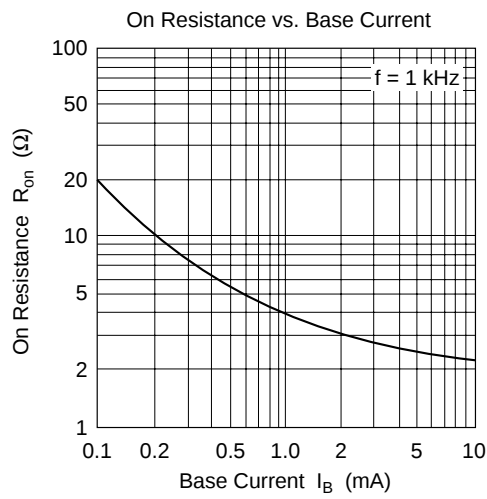
Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	12	V
Collector to emitter voltage	V_{CEO}	8	V
Emitter to base voltage	V_{EBO}	3	V
Collector current	I_C	50	mA
Collector power dissipation	P_C	150	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	−55 to +150	°C

Electrical Characteristics (Ta = 25°C)

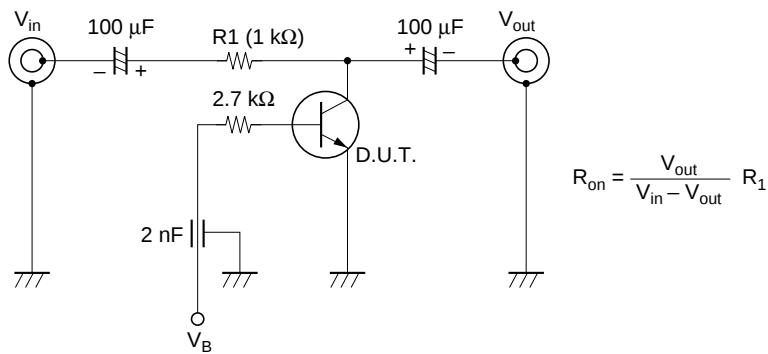
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	12	—	—	V	$I_C = 10\text{ }\mu\text{A}$, $I_E = 0$
Collector cutoff current	I_{CBO}	—	—	10	μA	$V_{CB} = 12\text{ V}$, $I_E = 0$
	I_{CEO}	—	—	1	mA	$V_{CE} = 8\text{ V}$, $R_{BE} = \infty$
Emitter cutoff current	I_{EBO}	—	—	10	μA	$V_{EB} = 3\text{ V}$, $I_C = 0$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	70	100	mV	$I_C = 20\text{ mA}$, $I_B = 4\text{ mA}$
DC current transfer ratio	h_{FE}	100	250	—		$V_{CE} = 5\text{ V}$, $I_C = 5\text{ mA}$
Collector output capacitance	C_{ob}	—	1.0	1.5	pF	$V_{CB} = 5\text{ V}$, $I_E = 0$, $f = 1\text{ MHz}$

Note: Marking is “XU—”.

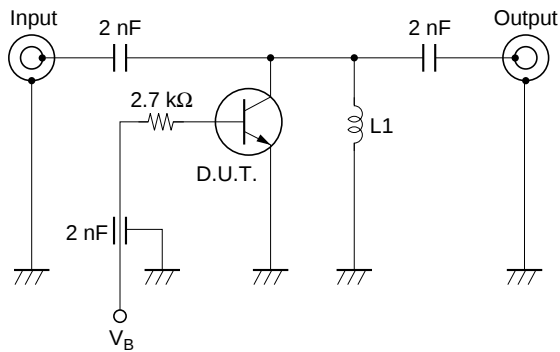




On Resistance Test Circuit

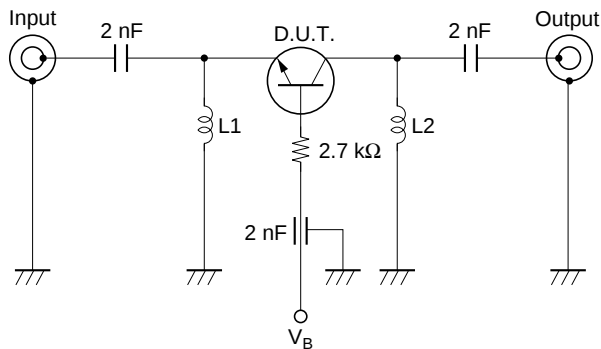


Reduction Test Circuit (Shunt Circuit)

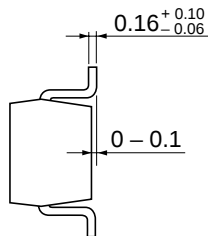
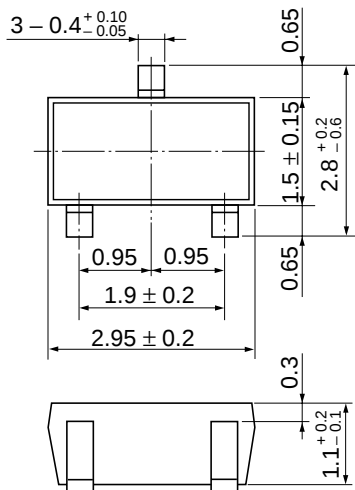


L1 : 3 mm inside dia, $\phi 0.2\ \text{mm}$ enameled copper wire, 15 turns

Reduction Test Circuit (Transfer Circuit)



L1, L2 : 3 mm inside dia, $\phi 0.2\ \text{mm}$ enameled copper wire, 15 turns



Hitachi Code	MPAK
JEDEC	—
EIAJ	Conforms
Weight (reference value)	0.011 g

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Hitachi, Ltd.

Semiconductor & Integrated Circuits.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

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For further information write to:

Hitachi Semiconductor (America) Inc. 179 East Tasman Drive, San Jose, CA 95134 Tel: <1> (408) 433-1990 Fax: <1> (408) 433-0223	Hitachi Europe GmbH Electronic components Group Dornacher Straße 3 D-85622 Feldkirchen, Munich Germany Tel: <49> (89) 9 9180-0 Fax: <49> (89) 9 29 30 00 Hitachi Europe Ltd. Electronic Components Group. Whitebrook Park Lower Cookham Road Maidenhead Berkshire SL6 8YA, United Kingdom Tel: <44> (1628) 585000 Fax: <44> (1628) 778322
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Hitachi Asia Pte. Ltd. 16 Collyer Quay #20-00 Hitachi Tower Singapore 049318 Tel: 535-2100 Fax: 535-1533 Hitachi Asia Ltd. Taipei Branch Office 3F, Hung Kuo Building, No.167, Tun-Hwa North Road, Taipei (105) Tel: <886> (2) 2718-3666 Fax: <886> (2) 2718-8180
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Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower, World Finance Centre,
Harbour City, Canton Road, Tsim Sha Tsui,
Kowloon, Hong Kong
Tel: <852> (2) 735 9218
Fax: <852> (2) 730 0281
Telex: 40815 HITEC HX

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